What is claimed is:

1. A method for fabricating a III-V nitride film, comprising the steps of:

preparing a substrate onto a susceptor in a reactor,

heating the substrate to a predetermined temperature,

coating an AlaGabIncN (a+b+c=1, a>0) film on an interior portion of a reactor which is heated to about 1000°C or over through the heating for the substrate, and

introducing a III raw material gas and a V raw material gas with a carrier gas onto the substrate prepared in the reactor, and thus, fabricating an AlxGayInzN (x+y+z=1) film by a MOCVD method.

2. A fabricating method as defined in claim 1, wherein the AlaGabIncN film is coated on the susceptor which is heated to about 1000°C or over.

3. A fabricating method as defined in claim 1, wherein the AlaGabIncN (a+b+c=1, a>0) film includes 50 atomic percentages or over of Al element (a>0.5) for all of the III elements.

4. A fabricating method as defined in claim 3, wherein the AlaGabIncN (a+b+c=1, a>0) film is composed of an AlN film.

5. A fabricating method as defined in claim 3, wherein the AlxGayInzN (x+y+z=1) film includes 50 atomic percentages or over of Al element (a>0.5) for all of the III elements.

6. A fabricating method as defined in claim 3, wherein the AlxGayInzN (x+y+z=1) film is composed of an AlN film.

7. An apparatus for fabricating a III-V nitride film by a MOCVD method, comprising:

a reactor in which the MOCVD reaction between a III raw material gas and a V material gas is generated,

a susceptor to hold a substrate thereon installed in the reactor,

a heater to heat the substrate to a predetermined temperature via the susceptor,

at least one of the interior wall of the reactor and the susceptor is coated with an AlaGabIncN (a+b+c=1, a>0) film, which is heated to 1000°C or over.

8. A fabricating apparatus as defined in claim 7, wherein the AlaGabIncN (a+b+c=1, a>0) film includes 50 atomic percentages or over of Al element (a>0.5) for all of the III elements.

9. A fabricating apparatus as defined in claim 8, wherein the AlaGabIncN

(a+b+c=1, a>0) film is composed of an AlN film.